



L940-__ _V Infrared LED Lamp

This series of L940-__ _V is a GaAs LED mounted on a lead frame and encapsulated in various types of epoxy lens which offer different design settings. On forward bias, it emits a high power radiation of typical 20mW with a peak wavelength at 940nm.

1) Specifications

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|---------------------|-------------------|
| (1) Chip material | GaAs |
| (2) Peak wavelength | 940nm |
| (3) Package | Clear epoxy resin |
| (4) Lead frame | Soldered |

2) Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	140	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	1000	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +85	°C	T _a =25°C
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

3) Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.30	1.45	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	16.0	20.0		mW
Peak Wavelength	λ _P	I _F =50mA		940		nm
Half Width	Δλ	I _F =50mA		50		nm
Rise Time	t _r	I _F =50mA		1000		ns
Fall Time	t _f	I _F =50mA		500		ns

4) Characteristics of Brightness [T_a=25°C]

Type	Viewing Half Angle	Radiant Intensity I _F =50mA unit: mW/sr			Outer Dimension	
		Minimum	Typical	Maximum	Dimension	Figure
L940-01V	±10°		65		f5	1
L940-02V	±5°		80		f5	2
L940-03V	±15°		55		f5	3
L940-04V	±20°		25		f5	4
L940-05V	±40°		7		f5	5
L940-06V	±7°		90		f5	6
L940-09V	±25°(Long)		40		f5	7
	±15°(Short)				Oval	
L940-33V	±15°		25		f3	9
L940-36V	±30°		13		f3	10

‡ Radiant Intensity is measured by Tektronix J-16.

‡ Total Radiated Power is measured by Photodyne #500.